IN THE CLAIMS:

1. (Previously presented) A laser irradiation method comprising:

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction; and

condensing said masked laser beam in a second direction orthogonal to said first direction after removing said portion to form a condensed laser beam, said condensed laser beam having a third cross section;

scanning an object with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

2. (Original) The method of claim 1 wherein the step of condensing said laser beam is done through a synthetic quartz lens.

3. (Original) The method of claim 1 wherein said laser is a pulse laser.

4. (Original) The method of claim 1 wherein said laser is an excimer laser.

5. (Cancelled)

6. (Previously presented) A laser irradiation method comprising:

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction; and

condensing said masked laser beam in a second direction orthogonal to said first direction after removing said portion to form a condensed laser beam, said condensed laser beam having a third cross section;

scanning an object with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction, and

wherein the length of the third cross section in the first direction is longer than a length of the first cross section in the first direction, and the width of the third cross section in the second direction is smaller than the width of the first cross section in the second direction.

7. (Original) The method of claim 6 wherein the step of condensing said laser beam is done through a synthetic quarts lens.

8. (Original) The method of claim 6 wherein said laser is a pulse laser.

9. (Original) The method of claim 6 wherein said laser is an excimer laser.

10. (Cancelled)

11. (Withdrawn) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section;

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film; and

scanning the semiconductor film with the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

12. (Withdrawn) The method of claim 11 wherein the step of condensing said laser beam is done through a synthetic quarts lens.

13. (Withdrawn) The method of claim 11 wherein said laser is a pulse laser.

14. – 16. (Cancelled)

17. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a substrate;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam.

18. (Cancelled).

19. (Withdrawn) The method according to claim 1 wherein said ion blocking film comprises silicon oxide.

20. (Currently amended) The method according to claim [[1]] <u>17</u> wherein said ion blocking film comprises silicon nitride.

21. (Currently amended) The method according to claim [[1]] <u>17</u> wherein said film formed over the ion blocking film comprises a transparent conductive oxide.

22. (Currently amended) The method according to claim [[1]] <u>17</u> wherein said ion blocking film is not doped with phosphorous.

23. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a glass substrate containing alkali ions;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam.

24. (Withdrawn) The method according to claim 23 wherein said laser beam is an excimer laser beam.

25. (Withdrawn) The method according to claim 23 wherein said ion blocking film comprises silicon oxide.

26. (Withdrawn) The method according to claim 23 wherein said ion blocking film comprises silicon nitride.

27. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a substrate wherein said ion blocking film has a thickness within a range of 50 to 1500 Å;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam.

28. (Withdrawn) The method according to claim 27 wherein said laser beam is an excimer laser beam.

29. (Withdrawn) The method according to claim 27 wherein said ion blocking film comprises silicon oxide.

30. (Withdrawn) The method according to claim 27 wherein said ion blocking film comprises silicon nitride.

31. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a glass substrate containing alkali ions wherein said ion blocking film has a thickness within a range of 50 to 1500 Å;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam.

32. (Currently amended) The method according to claim [[27]] 31 wherein said laser beam is an excimer laser beam.

33. (Currently amended) The method according to claim [[27]] 31 wherein said ion blocking film comprises silicon oxide.

34. (Currently amended) The method according to claim [[27]] 31 wherein said ion blocking film comprises silicon nitride.

35. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a substrate;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam,

wherein said laser beam is a pulsed laser beam and has a wavelength not longer than 400 nm.

36. (Withdrawn) The method according to claim 35 wherein said laser beam is an excimer laser beam.

37. (Withdrawn) The method according to claim 35 wherein said ion blocking film comprises silicon oxide.

38. (Withdrawn) The method according to claim 35 wherein said ion blocking film comprises silicon nitride.

39. (Withdrawn) The method according to claim 35 wherein said film formed over the ion blocking film comprises a transparent conductive oxide.

40. (Withdrawn) The method according to claim 35 wherein said ion blocking film is not doped with phosphorous.

41. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a glass substrate containing alkali ions;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam,

wherein said laser beam is a pulsed laser beam and has a wavelength not longer than 400 nm.

42. (Withdrawn) The method according to claim 41 wherein said laser beam is an excimer laser beam.

43. (Withdrawn) The method according to claim 41 wherein said ion blocking film comprises silicon oxide.

44. (Withdrawn) The method according to claim 41 wherein said ion blocking film comprises silicon nitride.

45. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a substrate wherein said ion blocking film has a thickness within a range of 50 to 1500 Å;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam,

wherein said laser beam is a pulsed laser beam and has a wavelength not longer than 400 nm.

46. (Withdrawn) The method according to claim 45 wherein said laser beam is an excimer laser beam.

47. (Withdrawn) The method according to claim 45 wherein said ion blocking film comprises silicon oxide.

48. (Withdrawn) The method according to claim 45 wherein said ion blocking film comprises silicon nitride.

49. (Withdrawn) A method comprising the steps of:

forming an ion blocking film over a glass substrate containing alkali ions wherein said ion blocking film has a thickness within a range of 50 to 1500 Å;

forming a film over the ion blocking film;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction in order to irradiate a surface of the film formed over the ion blocking film with a condensed laser beam having a second cross section at said surface,

wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section; and

moving said substrate along a third direction orthogonal to said first direction so that the surface of the film formed over the ion blocking film is scanned with the condensed laser beam,

wherein said laser beam is a pulsed laser beam and has a wavelength not longer than 400 nm.

50. (Withdrawn) The method according to claim 49 wherein said laser beam is an excimer laser beam.

51. (Withdrawn) The method according to claim 49 wherein said ion blocking film comprises silicon oxide.

52. (Withdrawn) The method according to claim 49 wherein said ion blocking film comprises silicon nitride.

53. (Withdrawn) The method according to claim 17 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

54. (Withdrawn) The method according to claim 23 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

55. (Withdrawn) The method according to claim 27 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

56. (Withdrawn) The method according to claim 31 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

57. (Withdrawn) The method according to claim 35 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

58. (Withdrawn) The method according to claim 41 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

59. (Withdrawn) The method according to claim 45 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of

condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

60. (Withdrawn) The method according to claim 49 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

61. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a substrate;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

62. (Previously presented) The method according to claim 61 wherein said laser beam is an excimer laser beam.

63. (Withdrawn) The method according to claim 61 wherein said ion blocking film comprises silicon oxide.

64. (Previously presented) The method according to claim 61 wherein said blocking film comprises silicon nitride.

65. (Withdrawn) The method according to claim 61 wherein said ion blocking film comprises non-doped silicon oxide.

66. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a substrate to a thickness of 1000 - 4000 Å;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

67. (Previously presented) The method according to claim 66 wherein said laser beam is an excimer laser beam.

68. (Withdrawn) The method according to claim 66 wherein said ion blocking film comprises silicon oxide.

69. (Previously presented) The method according to claim 66 wherein said blocking film comprises silicon nitride.

70. (Withdrawn) The method according to claim 66 wherein said ion blocking film comprises non-doped silicon oxide.

71. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a substrate;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section wherein said laser beam is a pulsed laser beam having a wavelength of not longer than 400 nm;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

72. (Previously presented) The method according to claim 71 wherein said laser beam is an excimer laser beam.

73. (Withdrawn) The method according to claim 71 therein said ion blocking film comprises silicon oxide.

74. (Previously presented) The method according to claim 71 wherein said blocking film comprises silicon nitride.

75. (Withdrawn) The method according to claim 71 wherein said ion blocking film comprises non-doped silicon oxide.

76. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a glass substrate containing alkali ions;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

77. (Previously presented) The method according to claim 76 wherein said laser beam is an excimer laser beam.

78. (Withdrawn) The method according to claim 76 wherein said ion blocking film comprises silicon oxide.

79. (Previously presented) The method according to claim 76 wherein said blocking film comprises silicon nitride.

80. (Withdrawn) The method according to claim 76 wherein said ion blocking film comprises non-doped silicon oxide.

81. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a glass substrate containing alkali ions to a thickness of 1000 - 4000 Å;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

82. (Previously presented) The method according to claim 81 wherein said laser beam is an excimer laser beam.

83. (Withdrawn) The method according to claim 81 wherein said ion blocking film comprises silicon oxide.

84. (Previously presented) The method according to claim 81 wherein said blocking film comprises silicon nitride.

85. (Withdrawn) The method according to claim 81 wherein said ion blocking film comprises non-doped silicon oxide.

86. (Previously presented) A method of manufacturing an active matrix display device having an active matrix circuit and a driving circuit, said method comprising:

forming an ion blocking film over a glass substrate containing alkali ions;

forming a semiconductor layer comprising amorphous silicon over said ion blocking film to a thickness of 200 - 1500 Å;

providing a first laser beam having a first cross section wherein said laser beam is a pulsed laser beam having a wavelength of not longer than 400 nm;

expanding said first cross section of the first pulsed laser beam in a first direction;

condensing the expanded laser beam in a second direction orthogonal to said first direction;

irradiating the semiconductor layer with the condensed laser beam having a second cross section at a surface of the semiconductor layer wherein a length of said second cross section in said first direction is longer than that of said first cross section and a width of said second cross section in said second direction is smaller than that of said first cross section;

moving said substrate along a third direction orthogonal to said first direction so that the semiconductor layer is scanned with the condensed laser beam and whereby the semiconductor layer is crystallized; and

forming a plurality of thin film transistors using the crystallized semiconductor layer as at least channel regions of the thin film transistors,

wherein both of the active matrix circuit and said driving circuit include said thin film transistors.

87. (Previously presented) The method according to claim 86 wherein said laser beam is an excimer laser beam.

88. (Withdrawn) The method according to claim 86 wherein said ion blocking film comprises silicon oxide.

89. (Previously presented) The method according to claim 86 wherein said blocking film comprises silicon nitride.

90. (Withdrawn) The method according to claim 86 wherein said ion blocking film comprises non-doped silicon oxide.

91. (Previously presented) The method according to claim 61 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

92. (Previously presented) The method according to claim 66 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

93. (Previously presented) The method according to claim 71 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

94. (Previously presented) The method according to claim 76 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

95. (Previously presented) The method according to claim 81 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

96. (Previously presented) The method according to claim 86 further comprising a step of removing a peripheral portion of the expanded laser beam through a mask before the step of condensing the expanded laser beam wherein said peripheral portion includes at least edges of the expanded laser beam extending in said first direction.

97. (Withdrawn) The method according to claim 23 wherein said glass substrate is a soda-lime glass.

98. (Withdrawn) The method according to claim 31 wherein said glass substrate is a soda-lime glass.

99. (Withdrawn) The method according to claim 41 wherein said glass substrate is a soda-lime glass.

100. (Withdrawn) The method according to claim 49 wherein said glass substrate is a soda-lime glass.

101. (Withdrawn) The method according to claim 76 wherein said glass substrate is a soda-lime glass.

102. (Previously presented) The method according to claim 81 wherein said glass substrate is a soda-lime glass.

103. (Previously presented) The method according to claim 86 wherein said glass substrate is a soda-lime glass.

104. (Previously presented) The method according to claim 61 wherein said active matrix display device is a liquid crystal device.

105. (Previously presented) The method according to claim 66 wherein said active matrix display device is a liquid crystal device.

106. (Previously presented) The method according to claim 71 wherein said active matrix display device is a liquid crystal device.

107. (Previously presented) The method according to claim 76 wherein said active matrix display device is a liquid crystal device.

108 (Previously presented) The method according to claim 81 wherein said active matrix display device is a liquid crystal device.

109. (Previously presented) The method according to claim 86 wherein said active matrix display device is a liquid crystal device.

Please add new claims 110-123 as follows:

110. (Previously presented) The method according to claim 1 wherein each of said first, second and third cross sections has a rectangular shape.

111. (Previously presented) The method according to claim 6 wherein each of said first, second and third cross sections has a rectangular shape.

112. (Withdrawn) The method according to claim 11 wherein each of said first, second and third cross sections.

113. (Withdrawn) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section;

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film; and

scanning the semiconductor film with respect to the condensed laser beam in a direction orthogonal to the first direction,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction, and

wherein the length of the third cross section in the first direction is longer than a length of the first cross section in the first direction, and the width of the third cross section in the second direction is smaller than the width of the first cross section in the second direction.

114. (Withdrawn) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam to form an expanded laser beam;

removing a portion of the expanded laser beam through a mask to form a masked laser beam;

condensing said masked laser beam to form a condensed laser beam after removing said portion; and

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film.

115. (Withdrawn) The method according to claim 114 wherein said laser beam is a pulsed laser beam.

116. (Withdrawn) The method according to claim 114 wherein said laser beam is a pulsed excimer laser beam.

117. (Withdrawn) The method according to claim 114 wherein said semiconductor film is formed over an ion blocking film formed on said substrate.

118. (Withdrawn) A method comprising:

forming a semiconductor film over a substrate;

emitting a laser beam wherein said laser beam has a first cross section;

expanding the first cross section of said laser beam in a first direction to form an expanded laser beam wherein said expanded laser beam has a second cross section;

removing a portion of said expanded laser beam through a mask to form a masked laser beam, said portion including at least edges of said expanded laser beam extending in said first direction;

condensing said masked laser beam in a second direction orthogonal to said first direction to form a condensed laser beam after removing said portion, said condensed laser beam having a third cross section; and

irradiating said semiconductor film with the condensed laser beam to crystallize said semiconductor film,

wherein a length of the third cross section in said first direction is longer than a width of the third cross section in said direction orthogonal to the first direction.

119. (Withdrawn) The method according to claim 118 wherein said laser beam is a pulsed laser beam.

120. (Withdrawn) The method according to claim 118 wherein said laser beam is a pulsed excimer laser beam.

121. (Withdrawn) The method according to claim 118 wherein the length of the third cross section in the first cross section is longer than a length of the first cross section in the first direction, and the width of the third cross section in the second direction is smaller than the width of the first direction in the second direction.

122. (Withdrawn) The method according to claim 118 wherein each of said first, second and third cross sections.

123. (Withdrawn) The method according to claim 118 wherein said semiconductor film is formed over an ion blocking film formed on said substrate.

124. (Withdrawn) The method according to claim 113 wherein each of said first, second and third cross sections has a rectangular shape.

125. (Withdrawn) The method according to claim 11 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500Å.

126. (Withdrawn) The method according to claim 113 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500Å.

127. (Withdrawn) The method according to claim 114 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500Å.

128. (Withdrawn) The method according to claim 118 wherein said semiconductor film comprises amorphous silicon and a thickness of said semiconductor film is 200 to 1500Å.

129. (Withdrawn) The method according to claim 17 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

130. (Withdrawn) The method according to claim 17 wherein said laser beam is a pulsed laser beam and said substrate is moved while one site of said film is irradiated with the condensed laser beam at a plurality of times.

131. (Previously presented) The method according to claim 61 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

132. (Previously presented) The method according to claim 1 wherein said laser beam is a pulsed laser beam and said object is moved with respect to the condensed laser beam in a stepwise manner.

133. (Previously presented) The method according to claim 6 wherein said laser beam is a pulsed laser beam and said object is moved.

134. (Currently amended) The method according to claim 1 wherein said laser beam is a pulsed laser beam and said object is moved while one side of said object is irradiated with the condensed laser beam [[at]] a plurality of times.

135. (Currently amended) The method according to claim 6 wherein said laser beam is a pulsed laser beam and said object is moved while one ~~site~~ side of said object is irradiated with the condensed laser beam [[at]] a plurality of times.

136. (Withdrawn) The method according to claim 11 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

137. (Withdrawn) The method according to claim 113 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

138. (Withdrawn) The method according to claim 114 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner.

139. (Withdrawn) The method according to claim 118 wherein said laser beam is a pulsed laser beam and said substrate is moved in a stepwise manner